imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832 Email & Skype: info@chipsmall.com Web: www.chipsmall.com Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

| V _{(BR)DSS} | R _{DS(on) max} | I _D T _A = +25°C | |
|----------------------|----------------------------------|--|--|
| 001/ | 8mΩ @ VGs = -10V | -17A | |
| -30V | 10.2mΩ @ V _{GS} = -4.5V | -14.5A | |

Description

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Power management functions
- Backlighting

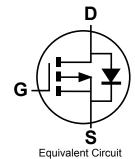
Features and Benefits

- Low Input Capacitance
- Low On-Resistance
- Fast Switching Speed
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.33 grams (approximate)





Pin-Out

G

D

D

Top View

Ordering Information (Note 4 & 5)

| Part Number | Compliance | Case | Packaging |
|----------------|------------|-------|-------------------|
| DMP3010LK3-13 | Standard | TO252 | 2,500/Tape & Reel |
| DMP3010LK3Q-13 | Automotive | TO252 | 2,500/Tape & Reel |

S

1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

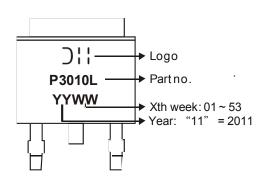
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html

Marking Information

Notes:





Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value -30 | Units V | | |
|--|------------------|--|-----------------|----------------|----|
| Drain-Source Voltage | V _{DSS} | | | | |
| Gate-Source Voltage | V _{GSS} | ±20 | V | | |
| | Steady State | T _A = +25°C T _A = +70°C | ID | -17.0 -13.0 | А |
| Continuous Drain Current (Note 7) V_{GS} = -10V | t<10s | T _A = +25°C T _A = +70°C | ID | -27.0 -21.0 | А |
| | Steady State | T _A = +25°C T _A = +70°C | ID | -14.5 -11.5 | А |
| Continuous Drain Current (Note 7) V_{GS} = -4.5V | t<10s | T _A = +25°C T _A = +70°C | ID | -23.0 -18.0 | А |
| Pulsed Drain Current (10µs pulse, duty cycle = 1%) | I _{DM} | -100 | А | | |
| Maximum Body Diode Forward Current (Note 7) | ls | 5.5 | А | | |
| Avalanche Current (Note 8) | I _{AS} | 47 | А | | |
| Avalanche Energy (Note 8) | | | E _{AS} | 113 | mJ |

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Units | |
|--|--------------|----------------------------------|-------------|------|
| Total Power Dissipation (Note 6) | PD | 1.7 | W | |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady state | P | 72 | °C/W |
| mermar Resistance, Junction to Ambient (Note 0) | t<10s | $R_{	heta}$ JA | 29 | °C/W |
| Total Power Dissipation (Note 7) | | PD | 3.4 | W |
| Thermal Decistence, Junction to Ambient (Note 7) | Steady state | P | 37 | °C/W |
| Thermal Resistance, Junction to Ambient (Note 7) | t<10s | $R_{	extsf{	heta}JA}$ | 15 | °C/W |
| Operating and Storage Temperature Range | | T _{J,} T _{STG} | -55 to +150 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|-----------------------------------|----------------------|--------|-------|-------|------|---|
| OFF CHARACTERISTICS (Note 9) | Symbol | IVIIII | тур | INIAX | Unit | Test condition |
| Drain-Source Breakdown Voltage | BV _{DSS} | -30 | _ | | V | V _{GS} = 0V, I _D = -250µA |
| Zero Gate Voltage Drain Current | I _{DSS} | | _ | -1 | μA | $V_{DS} = -30V, V_{GS} = 0V$ |
| Gate-Source Leakage | I _{GSS} | | _ | ±100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ |
| ON CHARACTERISTICS (Note 9) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | -1.1 | -1.6 | -2.1 | V | V _{DS} = V _{GS} , I _D = -250µA |
| Static Drain-Source On-Resistance | Р | _ | 6.5 | 8 | | V _{GS} = -10V, I _D = -10A |
| | R _{DS (ON)} | _ | 7.2 | 10.2 | mΩ | $V_{GS} = -4.5V, I_{D} = -10A$ |
| Forward Transfer Admittance | Y _{fs} | _ | 30 | _ | S | V _{DS} = -15V, I _D = -10A |
| Diode Forward Voltage | V _{SD} | _ | -0.65 | -1.0 | V | V _{GS} = 0V, I _S = -1A |
| DYNAMIC CHARACTERISTICS (Note 10) | | _ | | | | |
| Input Capacitance | C _{iss} | | 6234 | _ | | V _{DS} = 15V, V _{GS} = 0V f = 1.0MHz |
| Output Capacitance | Coss | _ | 1500 | | pF | |
| Reverse Transfer Capacitance | C _{rss} | _ | 774 | _ | | |
| Gate Resistance | R _G | _ | 1.28 | _ | μ | V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz |
| Total Gate Charge | Qg | _ | 59.2 | _ | | |
| Gate-Source Charge | Q _{gs} | _ | 16.1 | _ | nC | V _{DS} = -15V, V _{GS} = -4.5V, I _D = -10A |
| Gate-Drain Charge | Q _{gd} | _ | 15.7 | | | |
| Turn-On Delay Time | t _{D(on)} | _ | 11.4 | | | V _{DS} = -15V, V _{GEN} = -10V, |
| Turn-On Rise Time | tr | _ | 9.4 | _ | | |
| Turn-Off Delay Time | t _{D(off)} | _ | 260.7 | | ns | $R_G = 6\Omega, I_D = -1A$ |
| Turn-Off Fall Time | t _f | _ | 99.3 | | | |

Notes: 6. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.

7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

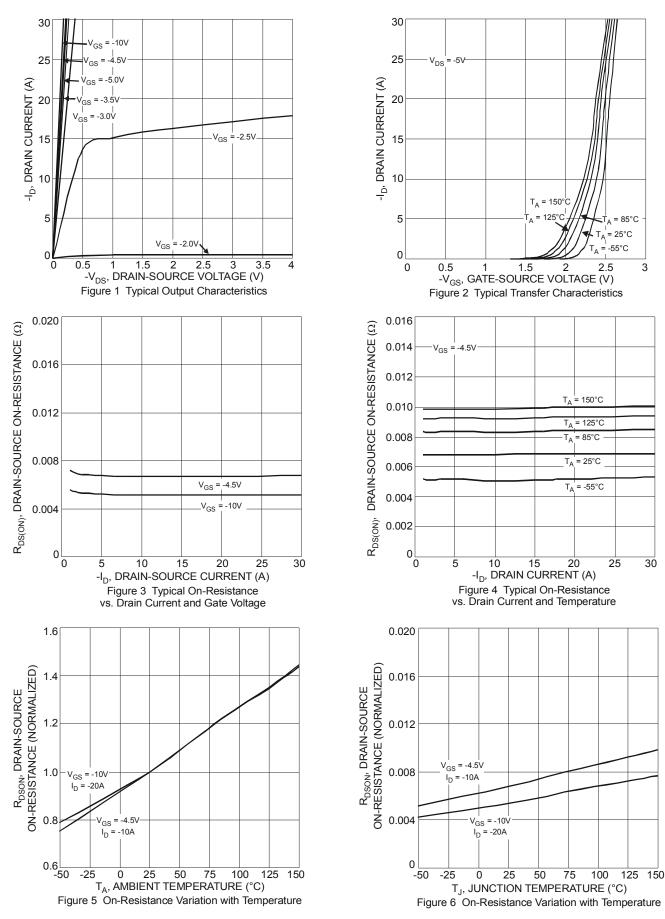
8 .UIS in production with L = 0.1mH, T_J = +25°C.

9. Short duration pulse test used to minimize self-heating effect.

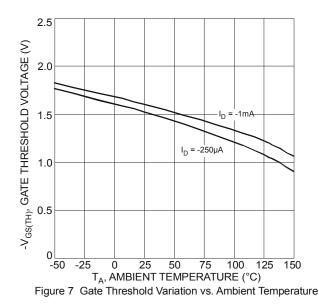
10. Guaranteed by design. Not subject to production testing.

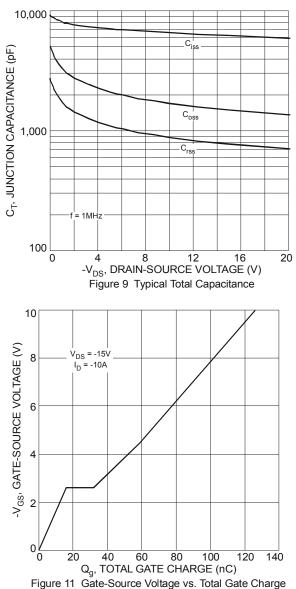
DMP3010LK3











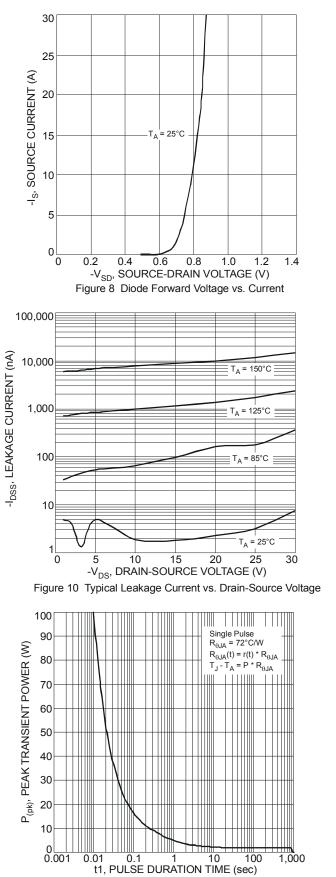
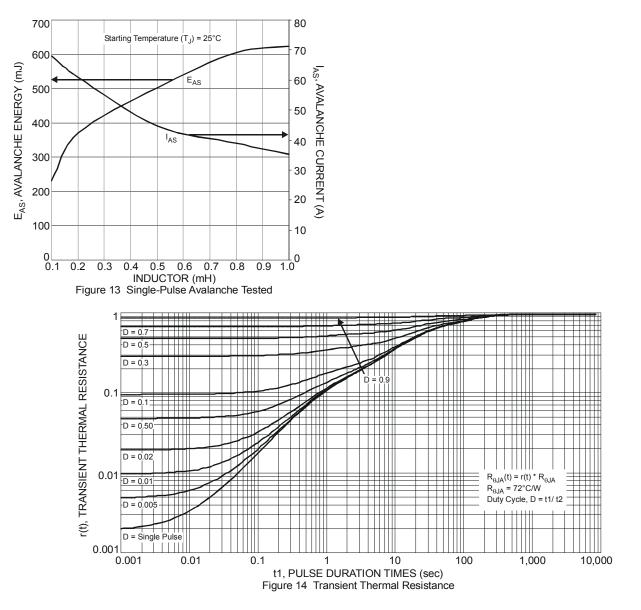


Figure 12 Single Pulse Maximum Power Dissipation

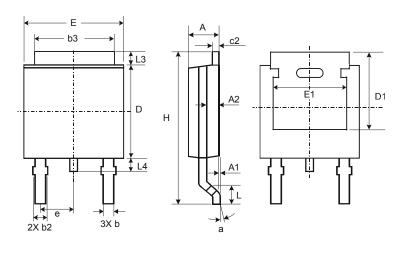






Package Outline Dimensions

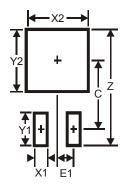
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



| | TO252 | | | | | | |
|-----|----------------------|-------|-------|--|--|--|--|
| Dim | Min | Max | Тур | | | | |
| Α | 2.19 | 2.39 | 2.29 | | | | |
| A1 | 0.00 | 0.13 | 0.08 | | | | |
| A2 | 0.97 | 1.17 | 1.07 | | | | |
| b | 0.64 | 0.88 | 0.783 | | | | |
| b2 | 0.76 | 1.14 | 0.95 | | | | |
| b3 | 5.21 | 5.46 | 5.33 | | | | |
| c2 | 0.45 | 0.58 | 0.531 | | | | |
| D | 6.00 | 6.20 | 6.10 | | | | |
| D1 | 5.21 | - | - | | | | |
| е | - | - | 2.286 | | | | |
| Е | 6.45 | 6.70 | 6.58 | | | | |
| E1 | 4.32 | - | - | | | | |
| Н | 9.40 | 10.41 | 9.91 | | | | |
| L | 1.40 | 1.78 | 1.59 | | | | |
| L3 | 0.88 | 1.27 | 1.08 | | | | |
| L4 | 0.64 | 1.02 | 0.83 | | | | |
| а | 0° | 10° | _ | | | | |
| All | All Dimensions in mm | | | | | | |

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 11.6 |
| X1 | 1.5 |
| X2 | 7.0 |
| Y1 | 2.5 |
| Y2 | 7.0 |
| C | 6.9 |
| E1 | 2.3 |



IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

A. Life support devices or systems are devices or systems which:

1. are intended to implant into the body, or

- 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2013, Diodes Incorporated

www.diodes.com